ETL SEMICONDUCTOR

Silicon PIN diode

BAP65 – 02

FEATURES

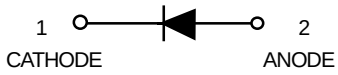
- High voltage, current controlled
- RF resistor for RF switches
- Low diode capacitance
- Low diode forward resistance (low loss)
- Very low series inductance.

APPLICATIONS

- RF attenuators and switches
- Bandswitch for TV tuners
- Series diode for mobile communication transmit/receive switch.

DESCRIPTION

Planar PIN diode in a SOD523 ultra small SMD plastic package.



SOD523 SC-79

LIMITING VALUES In accordance with the Absolute Maximum Rating System (IEC60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_R	continuous reverse voltage		–	30	V
I_F	continuous forward current		–	100	mA
P_{tot}	total power dissipation	$T_s \leq 90°C$	–	715	mW
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-65	+150	°C

ELECTRICAL CHARACTERISTICS $T_j = 25°C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_F	forward voltage	I_F=50 mA	0.9	1.1	V
I_R	reverse current	V_R=20 V	–	20	nA
C_d	diode capacitance	V_R= 0; f = 1 MHz	0.65	–	pF
		V_R= 1 V; f = 1 MHz	0.55	0.9	pF
		V_R= 3 V; f = 1 MHz	0.5	0.8	pF
		V_R= 20 V; f = 1 MHz	0.375	–	pF
r_D	diode forward resistance	I_F= 1 mA; f = 100 MHz;	1	–	Ω
		I_F= 5 mA; f = 100 MHz; note 1	0.65	0.95	Ω
		I_F= 10 mA; f = 100 MHz; note 1	0.56	0.9	Ω
		I_F= 100 mA; f = 100 MHz;	0.35	–	Ω
$\|s_{21}\|^2$	isolation	V_R= 0; f = 900 MHz	10	–	dB
		V_R= 0; f = 1800 MHz	5.8	–	dB
		V_R= 0; f = 2450 MHz	4.4	–	dB
$\|s_{21}\|^2$	insertion loss	I_F= 1 mA; f = 900 MHz	0.11	–	dB
		I_F= 1 mA; f = 1800 MHz	0.13	–	dB
		I_F= 1 mA; f = 2450 MHz	0.16	–	dB
$\|s_{21}\|^2$	insertion loss	I_F= 5 mA; f = 900 MHz	0.08	–	dB
		I_F= 5 mA; f = 1800 MHz	0.11	–	dB
		I_F= 5 mA; f = 2450 MHz	0.13	–	dB
$\|s_{21}\|^2$	insertion loss	I_F= 10 mA; f = 900 MHz	0.07	–	dB
		I_F= 10 mA; f = 1800 MHz	0.1	–	dB
		I_F= 10 mA; f = 2450 MHz	0.13	–	dB
$\|s_{21}\|^2$	insertion loss	I_F= 100 mA; f = 900 MHz	0.07	–	dB
		I_F= 100 mA; f = 1800 MHz	0.1	–	dB
		I_F= 100 mA; f = 2450 MHz	0.128	–	dB

ELECTRICAL CHARACTERISTICS T_j = 25°C unless otherwise specified. (Continue)

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
τ_L	charge carrier life time	when switched from I_F =10 mA to I_R = 6 mA; R_L = 100 Ω; measured at I_R =3 mA	0.17	–	µs
L_S	series inductance	I_F =10 mA ; f =100MHz	0.6	–	nH

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering-point	85	K/W

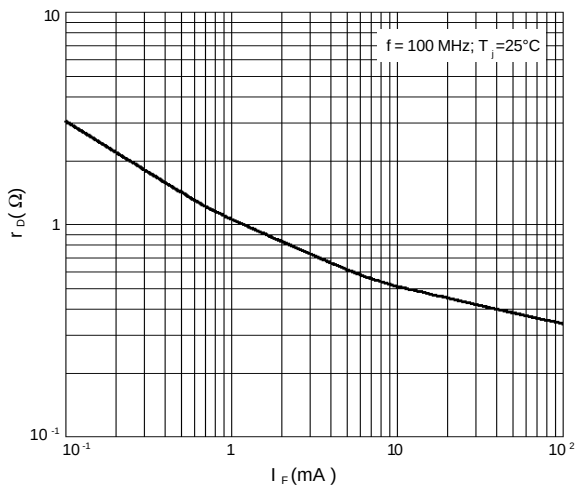


Fig.1 Forward resistance as a function of forward current; typical values.

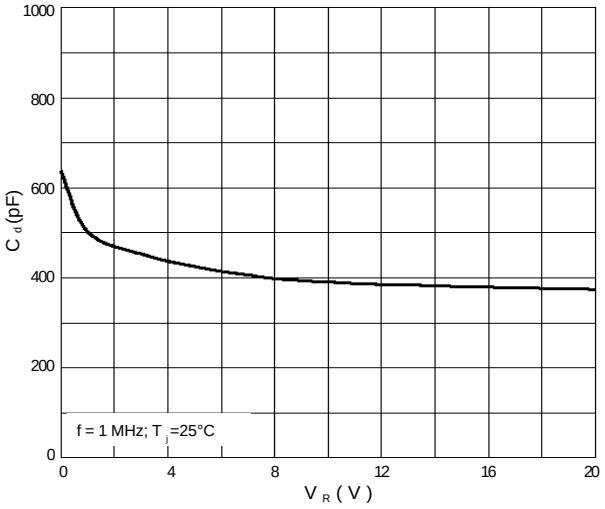


Fig.2 Diode capacitance as a function of reverse voltage; typical values.

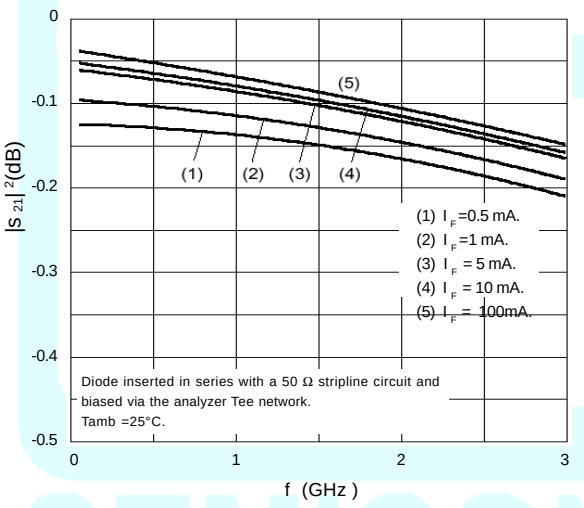


Fig.3 Insertion loss ($|s_{21}|^2$)of the diode in on-state as a function of frequency; typical values.

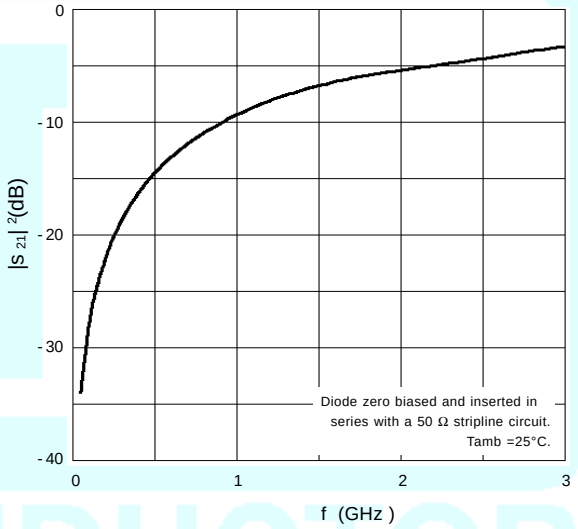


Fig.4 Isolation ($|s_{21}|^2$) of the diode in off-state as a function of frequency; typical values.